

AMENDMENTS TO THE SPECIFICATION

Please amend Paragraph [0043] of the specification to read as follows:

[0043] In an alternative embodiment of a solid state energy converter of the invention, thermal diode 10 of Figure 1 can be formed with p -type conductivity. Such an embodiment includes an emitter region 12 in thermal communication with a hot heat exchange surface, with the emitter region comprising a p -type region with acceptor concentration p^* for hole emission. A semiconductor gap region 18, with a ~~donor~~ acceptor doping p , is in electrical and thermal communication with emitter region 12. An n -type barrier layer 20 with donor concentration n^* is interposed between emitter region 12 and gap region 18. The p -type thermal diode can optionally include a collector region 22 in thermal communication with a cold heat exchange surface. A first ohmic contact is in electrical communication with emitter region 12 and a second ohmic contact is in electrical communication with collector region 22.